ABSTRACT OF THE DISCLOSURE

A transistor fin of a fin field-effect transistor is arranged between two contact structures. A gate electrode encapsulating the transistor fin on three sides is caused to recede by means of a nonlithographic process from contact trenches, which define the contact structures, before the formation of the contact structures. A distance a between the gate electrode and the contact structures is not subject to any tolerances due to the overlay of two independent lithographic masks. For a given extent of the gate electrode along the transistor fin, it is possible to minimize a distance A between the contact structures and thereby significantly increase the packing density of a plurality of fin field-effect transistors on a substrate compared with conventional devices.